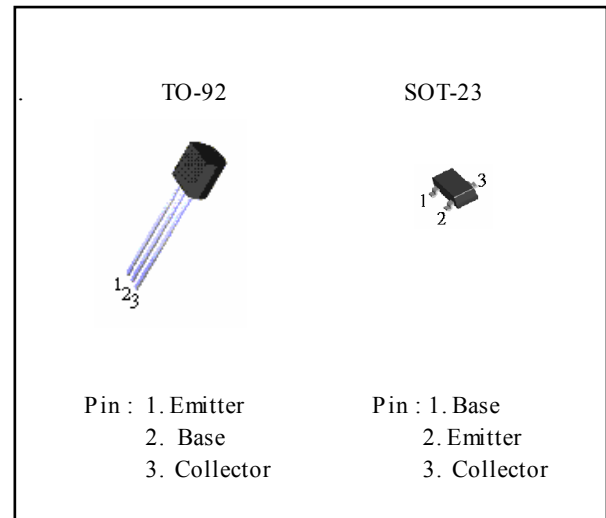


PNP Epitaxial Silicon Transistor

GENERAL PURPOSE TRANSISTOR

- Collector-Emitter Voltage: $V_{CEO} = 40V$
- Collector Dissipation: $P_C (max) = 625 mW$

**ABSOLUTE MAXIMUM RATINGS** ($T_a = 25^\circ C$)

Rating	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	40	V
Collector-Emitter Voltage	V_{CEO}	40	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	200	mA
Collector Dissipation	P_C	625	mW
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature	T_{stg}	-55~150	$^\circ C$

ORDERING INFORMATION

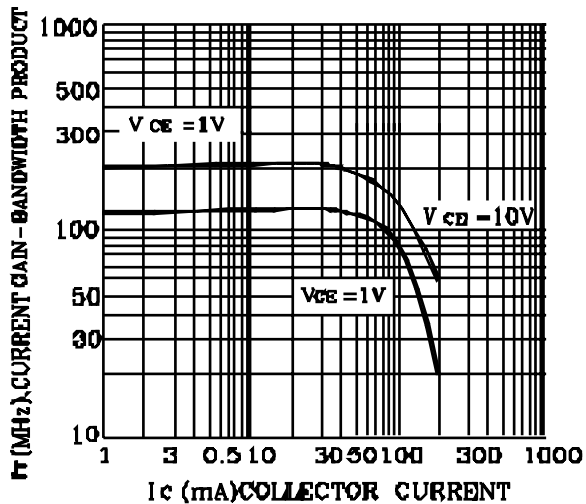
Device	Operating Temperature	Package
PJ2N3906CT	-20 $^\circ C$ ~ +85 $^\circ C$	TO-92
PJ2N3906CX		SOT-23

ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ C$)

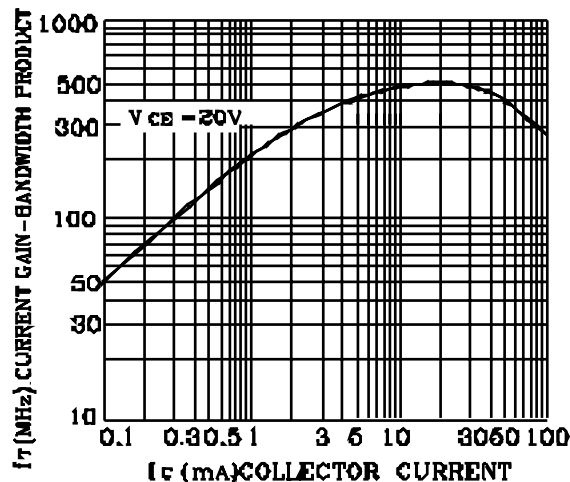
Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	BV_{CBO}	$I_C = 10 \mu A, I_E = 0$	40			V
*Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_C = 1mA, I_B = 0$	40			V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_E = 10 \mu A, I_C = 0$	6			V
Collector Cut-off Current	I_{CEX}	$V_{CE} = 30V, V_{BE} = 3V$			50	nA
Base Cut-off Current	I_{BL}	$V_{CE} = 30V, V_{BE} = 3V$			50	nA
*DC Current Gain	h_{FE}	$I_C = 0.1mA, V_{CE} = 1V$	60			
		$I_C = 1mA, V_{CE} = 1V$	80			
		$I_C = 10mA, V_{CE} = 1V$	100		300	
		$I_C = 50mA, V_{CE} = 1V$	60			
		$I_C = 100mA, V_{CE} = 1V$	30			
*Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 10mA, I_B = 1mA$			0.25	V
		$I_C = 50mA, I_B = 5mA$			0.4	V
*Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 10mA, I_B = 1mA$	0.65		0.85	V
		$I_C = 50mA, I_B = 5mA$			0.95	V
Output Capacitance	C_{ob}	$V_{CB} = 5V, I_E = 0$			4.5	pF
Current Gain Bandwidth Produce	f_T	$f = 1MHz$ $I_C = 10mA, V_{CE} = 20V$	250			MHz
Turn On Time	t_{on}	$f = 100MHz$ $V_{CC} = 3V, V_{BE} = 0.5V$			70	ns
Turn Off Time	t_{off}	$I_C = 10mA, I_{B1} = 1mA$ $V_{CC} = 3V, I_C = 1mA$ $I_{B1} = I_{B2} = 1mA$			250	ns

*Pulse Test: Pulse Width $\leq 300 \mu s$. Duty Cycle $\leq 2\%$

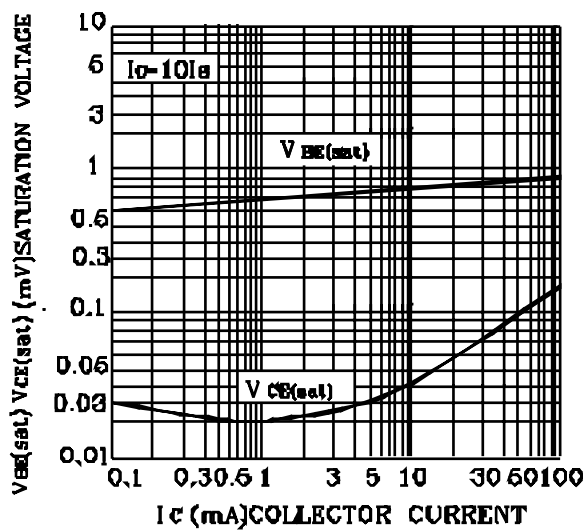
DC CURRENT GAIN



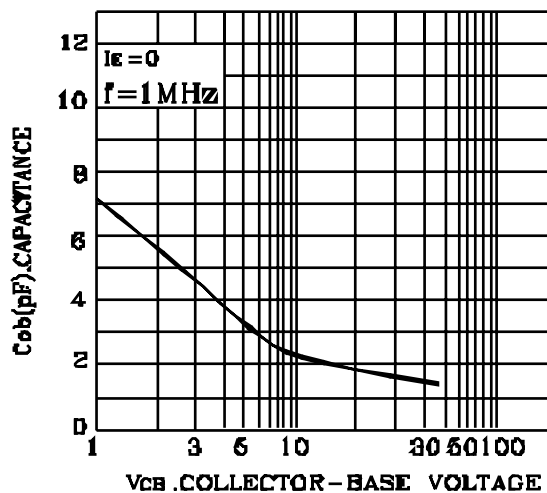
CURRENT GAIN-BANDWIDTH PRODUCT



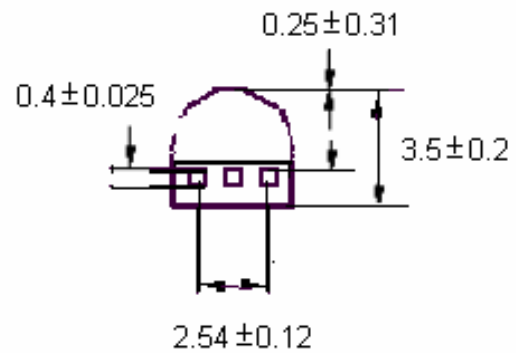
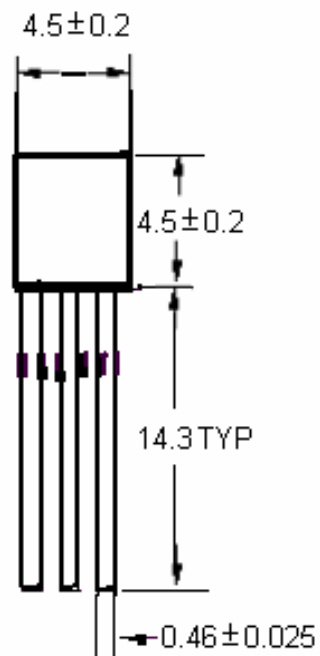
BASE-EMITTER SATURATION VOLTAGE
COLLECTOR-EMITTER SATURATION VOLTAGE



OUTPUT CAPACITANCE



TO-92 Unit:mm



SOT-23 Unit:mm

